

# RJP4007ANS

# Nch IGBT for Strobe Flash

REJ03G1866-0100 Rev.1.00 Dec 08, 2009

#### **Features**

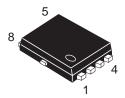
• Small surface mount package (VSON-8)

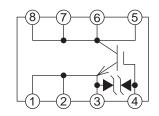
V<sub>CES</sub>: 400 VI<sub>CM</sub>: 150 A

• Drive voltage: 2.5 V to 6 V (MAX)

#### **Outline**

RENESAS Package code: PVSN0008JA-A (Package name: VSON-8<TNP-8DBV>)





1, 2, 3 : Emitter 4 : Gate

5, 6, 7, 8 : Collector

# **Applications**

Strobe flash for cameras

# **Maximum Ratings**

 $(Tc = 25^{\circ}C)$ 

| Parameter                 | Symbol           | Ratings     | Unit | Conditions                                |
|---------------------------|------------------|-------------|------|---|
| Collector-emitter voltage | V <sub>CES</sub> | 400         | V    | $V_{GE} = 0 V$                            |
| Gate-emitter voltage      | V <sub>GES</sub> | ±6          | V    | $V_{CE} = 0 V$                            |
| Collector current (Pulse) | I <sub>CM</sub>  | 150         | А    | $C_M = 200 \mu F$ (see performance curve) |
| Junction temperature      | Tj               | -40 to +150 | °C   |   |
| Storage temperature       | Tstg             | -40 to +150 | °C   |   |

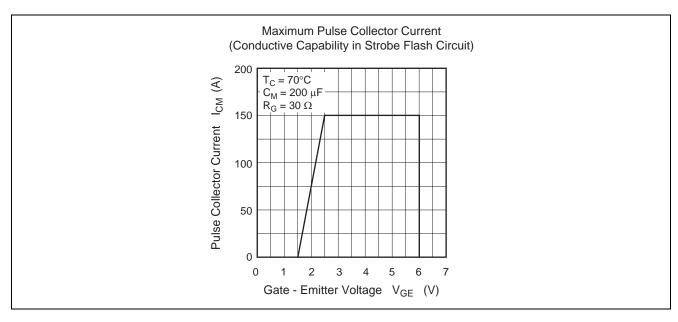
## **Electrical Characteristics**

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 $(Tj = 25^{\circ}C)$ 

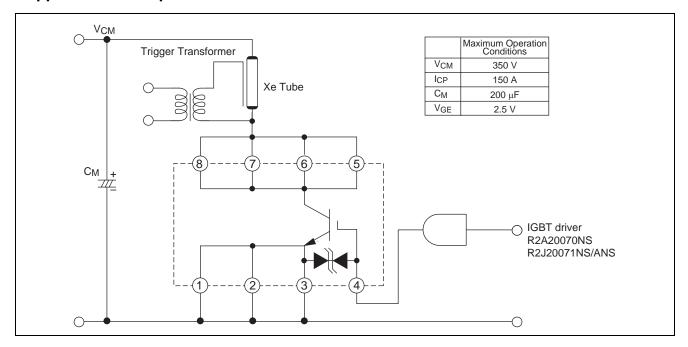
| Parameter                            | Symbol              | Min. | Тур. | Max. | Unit | Test conditions                                  |
|--------------------------------------|---------------------|------|------|------|------|--|
| Collector-emitter leakage current    | I <sub>CES</sub>    | _    | _    | 1    | μΑ   | $V_{CE} = 400 \text{ V}, V_{GE} = 0 \text{ V}$   |
| Gate-emitter leakage current         | I <sub>GES</sub>    | _    | _    | ±10  | μΑ   | $V_{GE} = \pm 6 \text{ V}, V_{CS} = 0 \text{ V}$ |
| Gate-emitter threshold voltage       | $V_{\text{GE(th)}}$ | 0.4  | 0.6  | 1.2  | V    | $V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$    |
| Collector-emitter saturation voltage | $V_{CE(sat)}$       | _    | 4.5  | 9.0  | V    | $I_C = 150 \text{ A}, V_{GE} = 2.5 \text{ V}$    |
| Input capacitance                    | Cies                | _    | 4000 | _    | рF   | $V_{CE} = 25 \text{ V}, V_{GE} = 10 \text{ V},$  |
|                                      |                     |      |      |      |      | f = 1 MHz  |

## **Performance Curves**



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# **Application Example**

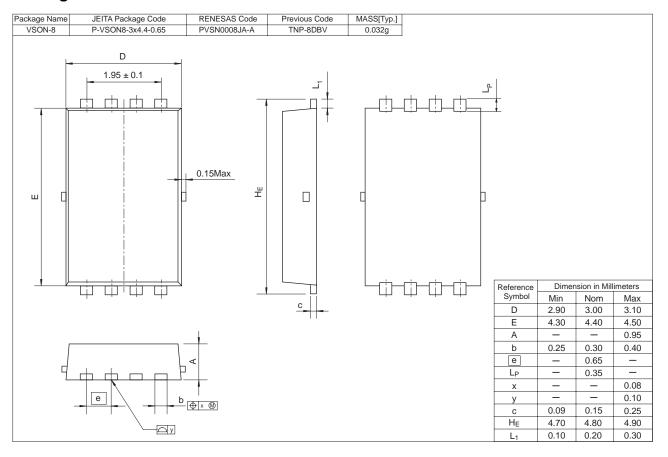


# **Precautions on Usage**

- 1. IGBT has MOS structure and its gate is insulated by thin silicon oxide. So please handle carefully to protect the device from electrostatic charge.
- 2. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current. And turn-off dv/dt must become less than 400 V/  $\mu s$ . In general, when  $R_{G \, (off)} = 30 \, \Omega$ , it is satisfied.
- 3. The operation life should be endured until repeated discharge of 5,000 times under the charge current ( $I_{Xe} \le 150~A$ : full luminescence condition) of main capacitor. Repetition period under full luminescence condition is over 3 seconds.

# **Package Dimensions**

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## **Order Code**

| Lead form            | Standard packing | Quantity | Standard order code | Standard order code example |
|----------------------|------------------|----------|---------------------|-----------------------------|
| Surface-mounted type | Taping           | 3000     | Type name – 00 – Q6 | RJP4007ANS-00-Q6            |

Note: Please confirm the specification about the shipping in detail.

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